TOSHIBA BI-CMOS INTEGRATED CIRCUIT SILICON MONOLITHIC

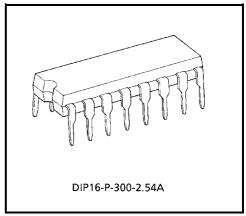
TB6501P

Bridge Driver with Rotation Detector

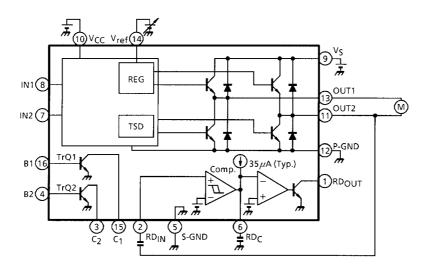
The TB6501P is Bridge Driver. Forward Rotation, Reverse Rotation, Stop and Breaking Operations are available.

FEATURES

- TB6501P has RD (Rotation Detector).
- Output current up to 0.4A (AVE.) to 1.0A (PEAK).
- Wide Range of Operating Supply Voltage
 - VCC (opr.) = 4.5~20 V VS (opr.) = 0~20 V
 - $V_{ref (opr.)} = 0 \sim 20 V (V_{ref} \le V_S)$
- Thermal shutdown, Over current protector, and Standby circuit built in.



Weight: 1.11g (Typ.)



BLOCK DIAGRAM

<u>TOSHIBA</u>

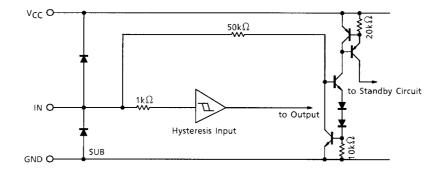
PIN FUNCTION

PIN No.	SYMBOL	FUNCTIONAL DESCRIPTION			
1	RD _{OUT}	Rotation detector output terminal			
2	RD _{IN}	Rotation detector input terminal			
3	C ₂	NPN transistor collector terminal			
4	B2	NPN transistor base terminal			
5	S-GND	Signal GND terminal			
6	RD _C	Rotation detector capacitor connection terminal			
7	IN2	Input 2 terminal			
8	IN1	IN1 Input 1 terminal			
9	V _S Power voltage supply terminal for motor driver				
10	0 V _{CC} Power voltage supply terminal for logic				
11	OUT2 Output 2 terminal				
12	P-GND	Power GND terminal			
13	OUT1	Output 1 terminal			
14	V _{ref}	Power voltage supply terminal for controller			
15	C ₁	NPN transistor collector terminal			
16	B1	NPN transistor base terminal			

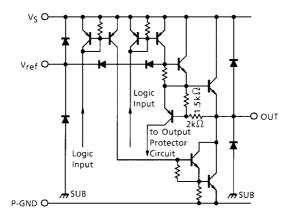
PIN CONNECTION

	_		
RDOUT	[1	16] B1
RDIN	2	15] c1
C2	E 3	14] V _{ref}
B2	[4	13] OUT1
S-GND	5	12] P-GND
RDC	6	11] OUT2
IN2	_ ۲	10] v _{cc}
IN1	8]	9] v _s
	-		1

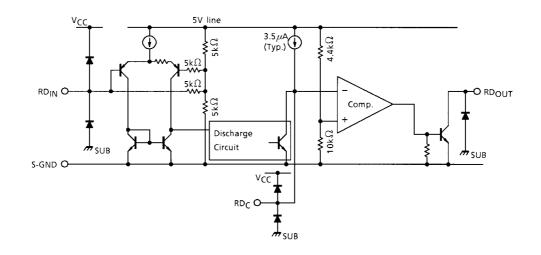
INPUT CIRCUIT



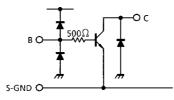
OUTPUT CIRCUIT



ROTATION DETECTOR CIRCUIT



TrQ1, TrQ2 CIRCUIT



FUNCTION

INF	νUT	OUT	PUT	MODE		
IN1	IN1 IN2		OUT2	MOTOR		
0	0	8	∞	STOP		
1	0	Н	L	CW / CCW		
0	1	L	Н	CCW / CW		
1	1	L	L	BRAKE		

∞: High Impedance

Note: Inputs are all high active type.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERI	STICS	SYMBOL	RATING	UNIT
Supply Voltage		V _{CC}	25	V
Motor Drive Voltage		VS	25	V
Reference Voltage		V _{ref}	25	V
	PEAK	I _{O (PEAK)}	1.0 (Note)	А
Output Current	AVE.	I _{O (AVE.)}	0.4	~
Output Ourfeilt	RD	I _{RD (PEAK)}	20 (Note)	mA
	TR	ITR (PEAK)	50 (Note)	
Power Dissipation		PD	1.2	W
Operating Temperature	!	T _{opr}	-30~75	°C
Storage Temperature		T _{stg}	-55~150	°C

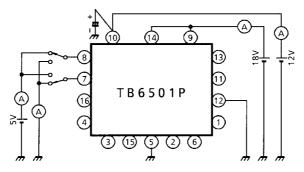
Note: $t = 0.1_s$

ELECTRICAL CHARACTERISTICS (Ta = 25°C, VCC = 12V, VS = 18V)

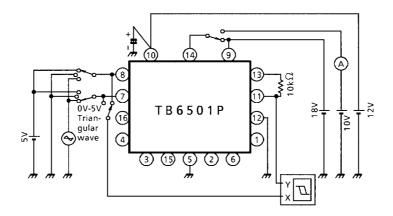
CHARACTERISTIC		SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN	TYP.	MAX	UNIT	
	I _{CC1}	—	Output open CW / CCW mode	_	8.2	12	mA		
	I _{CC2}	_	Output open STOP mode	_	400	750	μA		
		I _{CC3}	_	Output open BREAK mode	_	8.2	12	mA	
Supply Current	I _{S1}	_	Output open CW / CCW mode $V_{ref} = V_S$	_	5.2	11	mA		
	I _{S2}	—	Output open STOP mode $V_{ref} = V_S$	_	0	50	μA		
	I _{S3}	_	Output open BREAK mode $V_{ref} = V_S$	_	6.8	13	mA		
Input OperatiLng	1 (High)	V _{IN1}	—	T _j = 25°C	3.5	—	5.5	v	
Voltage	2 (Low)	V _{IN2}	—	T _j = 25°C	GND	_	0.8	V	
Input Current		I _{IN}	—	Sink V _{IN} = 5V	_	37	80	μA	
Input Hysteresis V	ΔV_T	—	—	_	0.55	_	V		
	V _{SAT U-1}	_		_	1.6	_	V		
	V _{SAT L-1}	—	$V_{ref} = V_S$ Output GND IO = 0.2 A CW / CCW mode	_	0.8	—	V		
Saturation Voltage		V _{SAT U-2}	_	$V_{ref} = V_S$ Output V_S $I_O = 0.4 A$ CW / CCW mode	-	1.75	2.3	V	
Saturation Voltage	V _{SAT L-2}	_	$V_{ref} = V_S$ Output GND $I_O = 0.4 A$ CW / CCW mode	_	0.9	1.3	V		
	V _{SAT U-3}	_	$V_{ref} = V_S$ Output V_S $I_O = 1.0 A$ CW / CCW mode	_	2.25	2.6	V		
	V _{SAT L-3}	_	$V_{ref} = V_S$ Output GND $I_O = 1.0 A$ CW / CCW mode	_	1.2	1.6	V		
Output Voltage	V _{SAT U-1} '	_	V _{ref} = 10 V Output GND I _O = 0.2 A CW / CW mode	9.3	10	10.7	V		
Oulput voltage	V _{SAT U-2'}	_	V _{ref} = 10 V Output GND I _O = 0.4 A CW / CCW mode	9.3	10	10.7	V		
Lashian Querrat		Ι _{LU}	—	V _L = 25 V	_	0	50		
Leaking Current		ILL	—	V _L = 25 V	—	0	50	μA	
	Upper	V _{F U-1}	—	I _F = 0.4 A	_	1.5	_		
Diode Forward	Opper	V _{F U-2}	_	I _F = 1 A	_	2.5	_	v	
Voltage	Lower	V _{F L-1}	—	I _F = 0.4 A	_	1.0	—		
		V _{F L-2}	—	I _F = 1 A	_	1.3	_	1	
Reference Current		I _{ref}	—	V _{ref} = 10 V Source Typ.	—	1	—	mA	
RD Output Saturation Voltage		V _{SAT RD}	_	I _{RD} = 5 mA	_	0.18	0.35	V	
TR Output Saturation Voltage		V _{SAT TR}	—	I _{TR} = 10 mA	—	4	0.65	V	
RDC Charge Current		I _{RDC}	_	_	21	35	55	μA	
RD Detective	Detective Level	R _{D (ON)}	—	AC coupling sine wave input	14	—	_	mV	
Sensitivity	Undetective Level	R _{D (OFF)}	—	RDC = 10 µF	_	_	7		
Thermal Shutdown Operating Temperature		T _{TSD}	_	Тј	160	_	_	°C	

TEST CIRCUIT 1

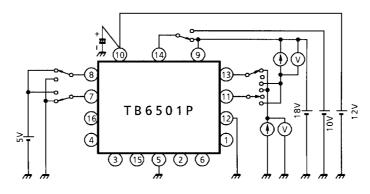
 $I_{CC1},\,I_{CC2},\,I_{CC3},\,I_{IN},\,I_{S1},\,I_{S2},\,I_{S3}$



TEST CIRCUIT 2 $V_{IN1}, V_{IN2}, \Delta V_T$

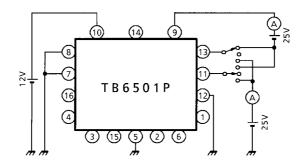


TEST CIRCUIT 3 VSAT U-1, 2, 3 VSAT L-1, 2, 3 VSAT U-1', 2'

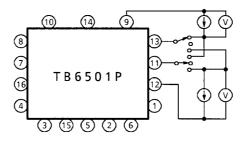


Note: Calibrate I_O to 0.2 / 0.4 / 1.0 A by R_L.

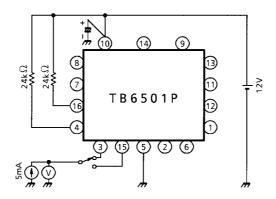
TEST CIRCUIT 4



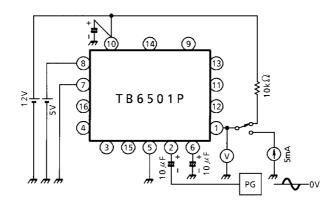
TEST CIRCUIT 5 VF U-1, 2 VF L-1, 2



TEST CIRCUIT 6 V_{SAT TR.}

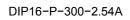


TEST CIRCUIT 7 V_{SAT RD} RD Sensitivity

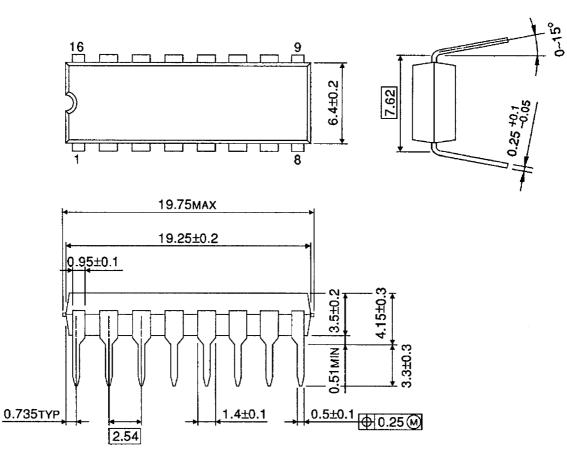


Note: Utmost care is necessary in the design of the output line, V_S, V_{CC} and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.

PACKAGE DIMENSIONS



Unit: mm



Weight: 1.11 g (Typ.)

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